STATUS OF THE CLAIMS

What is claimed is:

- (Original) A raised microstructure for use in a silicon based device, the raised microstructure comprising:
 - a generally planar thin-film;
 - a sidewall supporting the film;
 - wherein the sidewall has at least one rib formed therein.
- (Original) The raised microstructure of claim 1 wherein the sidewall is corrugated.
- 3. (Original) The raised microstructure of claim 1 wherein the rib has a generally arcuate cross section.
- (Currently Amended) The raised micro-structure microstructure of claim 1
 wherein the rib has a generally triangular cross section.
- (Original) The raised microstructure of claim 1 wherein the rib has a generally rectangular cross section.
- (Original) The raised microstructure of claim 1 wherein the thin-film comprises
 one plate of a silicon based capacitive transducer.
- 7. (Original) The raised microstructure of claim 1 wherein the thin-film comprises a rigid backplate of a silicon based microphone.

- 8. (Original) A silicon based electret microphone having a backplate comprising:
 a generally planar thin-film;
 a sidewall supporting the film;
 wherein the sidewall has at least one rib formed therein.
 - 9. (Original) The microphone of claim 8 wherein the sidewall is corrugated.
 - 10. (Original) The microphone of claim 8 wherein the rib has a generally arcuatecross section.
 - 11. (Currently Amended) The microphone of claim [[1]] 8 wherein the rib has a generally triangular cross section.
 - 12. (Currently Amended) The microphone of claim [[1]] 8 wherein the rib has a generally rectangular cross section.
 - 13. (Original) The microphone of claim 8 wherein the sidewall includes a plurality of ribs.
 - 14. (Original) The microphone of claim 13, wherein the ribs are equally spaced about the sidewall.

15. (Original) A raised microstructure for use in a silicon based device, the raised microstructure comprising:

generally planar element with a first thickness and a periphery;

a sidewall with a second thickness;

said sidewall supporting said planar element at said periphery above a substrate at a distance;

wherein said sidewall has a plurality of ribs formed therein.

- 16. (Original) The raised microstructure of claim 15 wherein said first thickness is small compared to the lateral extent of the said planar element.
- 17. (Original) The raised microstructure of claim 15 wherein said second thickness is approximately equal to the said first thickness.
- 18. (Original) The raised microstructure of claim 15 wherein said distance is large compared to said second thickness.
- 19. (Original) The raised microstructure of claim 15 wherein the ribs follow a periodic path of the periphery, inwards and outwards with respect to the centroid of the planar element.
- 20. (Original) The raised microstructure of claim 19 wherein the path is arcuate.
- 21. (New) The raised microstructure of claim 1 wherein the sidewall substantially completely encloses the area beneath the thin-film.

22. (New) The microphone of claim 8 wherein the sidewall substantially completely encloses the area beneath the thin-film.

23. (New) The raised microstructure of claim 15 wherein the sidewall substantially completely encloses the area beneath the element.